

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1.- 12. (Canceled)

13. (Currently Amended) A vapor reaction method comprising the steps of:  
providing a pair of first and second electrodes within a reaction chamber, said pair of electrodes being arranged substantially in parallel with each other;  
placing a substrate in the reaction chamber ~~on said first electrode~~ wherein said substrate is held by said first electrode so that a first surface of said substrate faces toward said second electrode;  
introducing a first film forming gas into said reaction chamber through said second electrode;  
exciting said first film forming gas in order to form a first insulating film by first vapor deposition on said substrate placed in said reaction chamber wherein said first insulating film comprises silicon nitride;  
introducing a second film forming gas into said reaction chamber through said second electrode;  
exciting said second film forming gas in order to form a second insulating film by a second vapor deposition directly on said first insulating film in said reaction chamber wherein said first and second insulating films contact each other;  
removing said substrate from said reaction chamber after the formation of the first and second insulating films;  
introducing a cleaning gas comprising nitrogen fluoride into said reaction chamber through said second electrode;  
exciting said cleaning gas in order to remove unnecessary layers caused the first and second vapor depositions from an inside of the reaction chamber,  
~~wherein one of the first and second insulating films comprises silicon nitride and the other one of the first and second insulating films~~ the second insulating film comprises a

different material from the first insulating film ~~said one of the first and second insulating films.~~

14.- 16. (Canceled)

17. (Currently Amended) A vapor reaction method comprising the steps of:  
providing a pair of first and second electrodes within a reaction chamber, said pair of electrodes being arranged substantially in parallel with each other;  
placing a substrate in a reaction chamber on said first electrode so that a first surface of said substrate faces toward said second electrode;  
introducing a first film forming gas into said reaction chamber through said second electrode;  
exciting said first film forming gas in order to form a first film comprising silicon nitride by vapor deposition on said substrate placed in said reaction chamber;  
introducing a second film forming gas into said reaction chamber through said second electrode;  
exciting said second film forming gas in order to form a second film ~~by vapor deposition~~ by vapor deposition directly on said first film in said reaction chamber;  
removing said substrate from said reaction chamber after the formation of the first and second films;  
introducing a cleaning gas comprising nitrogen fluoride into said reaction chamber through said second electrode;  
exciting said cleaning gas in order to remove unnecessary layers formed on an inside of the reaction chamber due to the formation of the first and second films.

18.-20. (Canceled)

21. (Currently Amended) A method of fabricating electronic devices comprising the steps of:  
providing a pair of electrodes within a reaction chamber wherein said pair of electrodes are opposed in parallel with each other;

placing a substrate in a reaction chamber wherein said substrate is ~~held by one of said electrodes~~ placed on said pair of electrodes so that a first surface of said substrate faces toward said second electrode;

introducing a first film forming gas into said reaction chamber through the other one of said electrodes;

exciting said first film forming gas to form a first film comprising silicon nitride by first chemical vapor deposition on said substrate;

introducing a second film forming gas into said reaction chamber through the other one of said electrodes;

exciting said second film forming gas to form a second film by second chemical vapor deposition directly on said first film, said second film comprising a different material from said first film;

removing said substrate from said reaction chamber after the formation of said first and second films;

introducing a cleaning gas comprising nitrogen fluoride into said reaction chamber through said other one of the electrodes; and

conducting a cleaning of an inside of said reaction chamber by using said cleaning gas to remove layers caused by at least said first and second vapor phase deposition[[],].

~~wherein one of the first and second films comprises silicon nitride.~~

22. (Currently Amended) [[A]] The method according to claim 21 wherein said first chemical vapor deposition is a photo CVD.

23. (Currently Amended) [[A]] The method according to claim 21 wherein said second chemical vapor deposition is a plasma CVD.

24. (Currently Amended) [[A]] The method according to claim 21 wherein said cleaning gas is excited by said pair of electrodes.

25. (Currently Amended) [[A]] The method according to claim 21 wherein said other one of the electrodes is provided with a plurality of ports for introducing said cleaning gas into the reaction chamber.

26. (Currently Amended) A method of fabricating electronic devices comprising the steps of:

providing a pair of electrodes within a reaction chamber wherein said pair of electrodes are opposed in parallel with each other;

placing a substrate in a reaction chamber wherein said substrate is held by one of said electrodes so that a first surface of said substrate faces toward said second electrode;

introducing a first film forming gas into said reaction chamber through the other one of said electrodes;

exciting said first film forming gas to form a first film comprising silicon nitride by first chemical vapor deposition on said substrate;

introducing a second film forming gas into said reaction chamber through the other one of said electrodes;

exciting said second film forming gas to form a second film by second chemical vapor deposition directly on said first film wherein said second film comprises a different material from said first film;

removing said substrate from said reaction chamber after the formation of said first and second films;

introducing a cleaning gas comprising nitrogen fluoride into said reaction chamber through said other one of the electrodes; and

conducting a cleaning of an inside of said reaction chamber by using said cleaning gas to remove layers caused by at least said first and second vapor phase deposition,

wherein one of the first and second films comprises silicon nitride.

27. (Currently Amended) [[A]] The method according to claim 26 wherein said first chemical vapor deposition is a photo CVD.

28. (Currently Amended) [[A]] The method according to claim 26 wherein said second chemical vapor deposition is a plasma CVD.

29. (Currently Amended) [[A]] The method according to claim 26 wherein said cleaning gas is excited by said pair of electrodes.

30. (Currently Amended) [[A]] The method according to claim 26 wherein said other one of the electrodes is provided with a plurality of ports for introducing said cleaning gas into the reaction chamber.

31. (New) The vapor reaction method according to claim 13 wherein said first vapor deposition is a photo CVD.

32. (New) The vapor reaction method according to claim 13 wherein said second vapor deposition is a plasma CVD.

33. (New) The vapor reaction method according to claim 13 wherein said second electrode is provided with a plurality of ports for introducing said cleaning gas into the reaction chamber.

34. (New) The vapor reaction method according to claim 17 wherein said first vapor deposition is a photo CVD.

35. (New) A method according to claim 17 wherein said second vapor deposition is a plasma CVD.

36. (New) A method according to claim 17 wherein said second electrode is provided with a plurality of ports for introducing said cleaning gas into the reaction chamber.